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Dual 30-V N-Channel NexFET™ Power MOSFETs

FEATURES

- Common Source Connection
- Ultra Low Drain to Drain On-Resistance
- Space Saving SON 3.3 x 3.3mm Plastic Package
- Optimized for 5V Gate Drive
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free

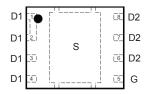
APPLICATIONS

 Adaptor/USB Input Protection for Notebook PCs and Tablets

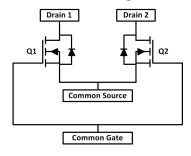
DESCRIPTION

The CSD87312Q3E is a 30V common-source, dual N-channel device designed for adaptor/USB input protection. This SON 3.3 x 3.3mm device has low drain to drain on-resistance that minimizes losses and offers low component count for space constrained multi-cell battery charging applications.

Top View



Circuit Image



PRODUCT SUMMARY

| T _A = 25° | С | TYPICAL VA | UNIT | |
|----------------------|------------------------------|-------------------------|------|----|
| V_{DS} | Drain to Source Voltage | 30 | V | |
| Q_g | Gate Charge Total (4.5V) | 6.3 | | nC |
| Q_{gd} | Gate Charge Gate to Drain | 0.7 | nC | |
| 0 | Drain to Drain On Resistance | $V_{GS} = 4.5V$ | 31 | mΩ |
| R _{DD(on)} | (Q1+Q2) | V _{GS} = 8V 27 | | mΩ |
| V _{GS(th)} | Threshold Voltage | 1.0 | ٧ | |

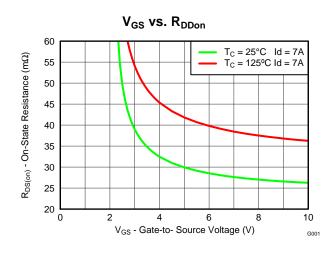
ORDERING INFORMATION

| Device | Package | Media | Qty | Ship | |
|-------------|------------------------------------|-----------------|------|------------------|--|
| CSD87312Q3E | SON 3.3 x 3.3mm Plastic Package | 13-Inch Reel | 2500 | Tape and Reel | |

ABSOLUTE MAXIMUM RATINGS

| $T_A = 2$ | 5°C | VALUE | UNIT | | | | | | |
|-------------------|--|------------|------|--|--|--|--|--|--|
| V_{DS} | Drain to Source Voltage | 30 | V | | | | | | |
| V_{GS} | Gate to Source Voltage | +10/-8 | V | | | | | | |
| I _D | Continuous Drain Current, T _C = 25°C ⁽¹⁾ | 27 | Α | | | | | | |
| I_{DM} | Pulsed Drain Current (2) | 45 | Α | | | | | | |
| P_D | Power Dissipation | 2.5 | W | | | | | | |
| T_J , T_{STG} | Operating Junction and Storage Temperature Range | -55 to 150 | °C | | | | | | |
| E _{AS} | Avalanche Energy, single pulse I_D = 24A, L = 0.1mH, R_G = 25 Ω | 29 | mJ | | | | | | |

- (1) Typical R = 63° C/W on 1in² (2 oz.) on 0.060" thick FR4PCB
- (2) Pulse duration ≤300µs, duty cycle ≤2%



A

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|------------------------------------|---|-----|------|------|------|
| Static CI | naracteristics | | | | | |
| BV _{DSS} | Drain to Source Voltage | $V_{GS} = 0V, I_D = 250\mu A$ | 30 | | | V |
| I _{DSS} | Drain to Source Leakage Current | $V_{GS} = 0V, V_{DS} = 24V$ | | | 1 | μΑ |
| I _{GSS} | Gate to Source Leakage Current | $V_{DS} = 0V, V_{GS} = +10/-8V$ | | | 100 | nA |
| V _{GS(th)} | Gate to Source Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 0.8 | 1.0 | 1.3 | V |
| D | Drain to Drain On Resistance (Q1 + | $V_{GS} = 4.5V, I_D = 7A$ | | 31 | 38 | mΩ |
| R _{DD(on)} | Q2) | $V_{GS} = 8V$, $I_D = 7A$ | | 27 | 33 | mΩ |
| 9 _{fs} | Transconductance | $V_{DS} = 15V, I_{D} = 7A$ | | 39 | | S |
| Dynamic | : Characteristics ⁽¹⁾ | | | | | |
| C _{iss} | Input Capacitance | | | 960 | 1250 | pF |
| C _{oss} | Output Capacitance | $V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$ | | 190 | 247 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 12 | 16 | pF |
| R_G | Series Gate Resistance | | | 5 | 10 | Ω |
| Qg | Gate Charge Total (4.5V) | | | 6.3 | 8.2 | nC |
| Q_{gd} | Gate Charge Gate to Drain | \/ 45\/ 70 | | 0.7 | | nC |
| Q _{gs} | Gate Charge Gate to Source | $V_{DS} = 15V, I_D = 7A$ | | 1.9 | | nC |
| Q _{g(th)} | Gate Charge at Vth | | | 1.0 | | nC |
| Q _{oss} | Output Charge | V _{DS} = 15V, V _{GS} = 0V | | 4.0 | | nC |
| t _{d(on)} | Turn On Delay Time | | | 7.8 | | ns |
| t _r | Rise Time | V 45V V 45V L 7A B 20 | | 16 | | ns |
| t _{d(off)} | Turn Off Delay Time | $V_{DS} = 15V, V_{GS} = 4.5V, I_{DS} = 7A, R_G = 2\Omega$ | | 17 | | ns |
| t _f | Fall Time | | | 2.9 | | ns |
| Diode C | haracteristics ⁽¹⁾ | | | | , | |
| V _{SD} | Diode Forward Voltage | I _{SD} = 7A, V _{GS} = 0V | | 0.8 | 1 | V |
| Q _{rr} | Reverse Recovery Charge | V 45V L 7A 4:/4t 200A/ | | 5.3 | | nC |
| t _{rr} | Reverse Recovery Time | V_{DS} = 15V, I_F = 7A, di/dt = 300A/ μ s | | 12.2 | | ns |
| | | | • | | | |

⁽¹⁾ All Dynamic and Diode Characteristics were measured with respect to one of the two drains, with the other left floating.

THERMAL CHARACTERISTICS

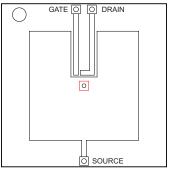
(T_A = 25°C unless otherwise stated)

| | PARAMETER | MIN | TYP | MAX | UNIT |
|-----------------|--|-----|-----|-----|------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case ⁽¹⁾ | | | 4.2 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾ | | | 63 | °C/W |

 ⁽¹⁾ R_{θ,JC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θ,JC} is specified by design, whereas R_{θ,JA} is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

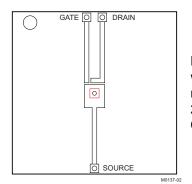
RUMENTS





Instruments

Max $R_{\theta JA} = 63^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 165^{\circ}\text{C/W}$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

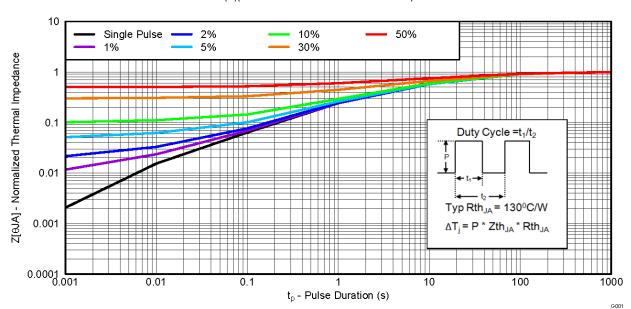
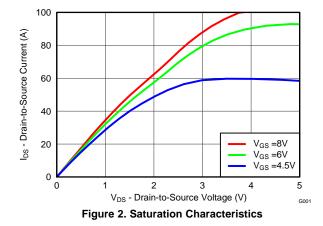


Figure 1. Transient Thermal Impedance



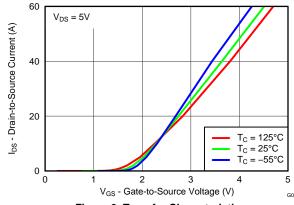


Figure 3. Transfer Characteristics

TEXAS INSTRUMENTS

TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

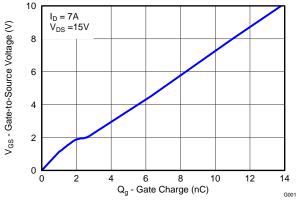


Figure 4. Gate Charge

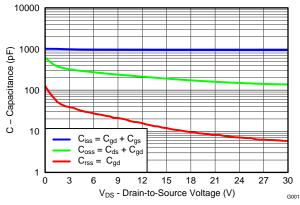


Figure 5. Capacitance

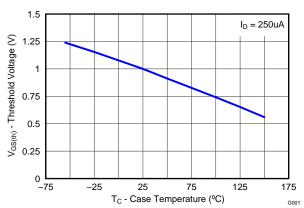


Figure 6. Threshold Voltage vs. Temperature

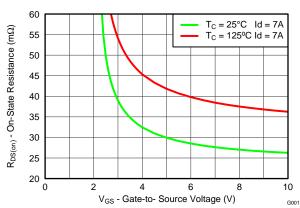


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

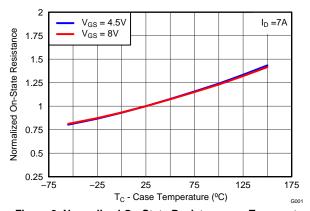


Figure 8. Normalized On-State Resistance vs. Temperature

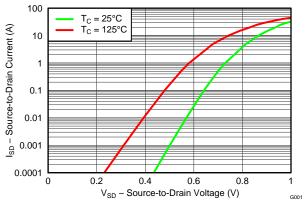


Figure 9. Typical Diode Forward Voltage



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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

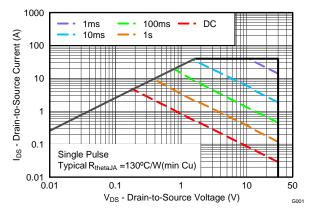


Figure 10. Maximum Safe Operating Area

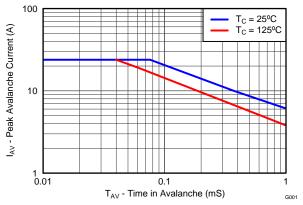


Figure 11. Single Pulse Unclamped Inductive Switching

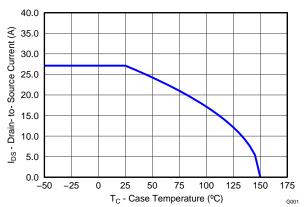
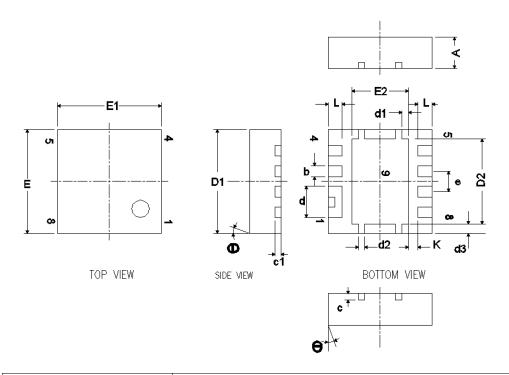


Figure 12. Maximum Drain Current vs. Temperature



MECHANICAL DATA

Q3E Package Dimensions



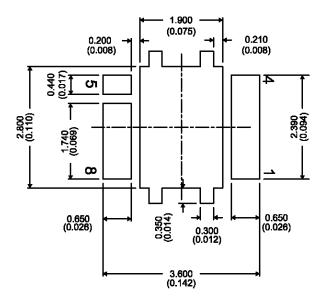
| DIM | MILLIMETERS | | | | | |
|-----|-------------|--------|--|--|--|--|
| DIM | MIN | MAX | | | | |
| Α | 0.850 | 1.050 | | | | |
| b | 0.280 | 0.400 | | | | |
| С | 0.150 | 0.250 | | | | |
| c1 | 0.150 | 0.250 | | | | |
| d | 0.940 | 1.040 | | | | |
| d1 | 0.160 | 0.260 | | | | |
| d2 | 0.150 | 0.250 | | | | |
| d3 | 0.250 | 0.350 | | | | |
| D1 | 3.200 | 3.400 | | | | |
| D2 | 2.650 | 2.750 | | | | |
| E | 3.200 | 3.400 | | | | |
| E1 | 3.200 | 3.400 | | | | |
| E2 | 1.750 | 1.850 | | | | |
| е | 0.68 | 50 TYP | | | | |
| L | 0.400 | 0.500 | | | | |
| θ | 0° | - | | | | |
| K | 0.300 Typ | | | | | |

Notes:

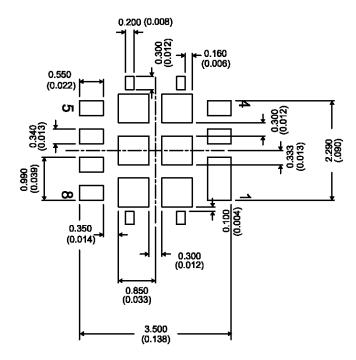
- 1. Pin 1-4: Drain 1
- 2. Pin 5: Gate
- 3. Pin 6-8: Drain 2
- 4. Pin 9: Source

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Recommended PCB Pattern



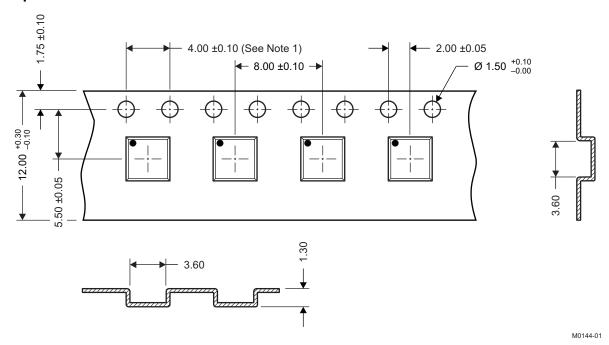
Recommended Stencil Opening



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.



Q3E Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible

11-Nov-2025

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PACKAGING INFORMATION

| Orderable part number | Status | Material type | Package Pins | Package qty Carrier | RoHS (3) | Lead finish/ Ball material | MSL rating/ Peak reflow | Op temp (°C) | Part marking (6) |
|-----------------------|--------|---------------|----------------|-----------------------|-----------------|-------------------------------|----------------------------|--------------|------------------|
| CSD87312Q3E | Active | Production | VSON (DPA) 8 | 2500 LARGE T&R | ROHS Exempt | NIPDAU | Level-1-260C-UNLIM | -55 to 150 | 87312E |
| CSD87312Q3E.B | Active | Production | VSON (DPA) 8 | 2500 LARGE T&R | ROHS Exempt | NIPDAU | Level-1-260C-UNLIM | -55 to 150 | 87312E |

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

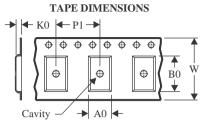
⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





| A0 | Dimension designed to accommodate the component width |
|----|---|
| В0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

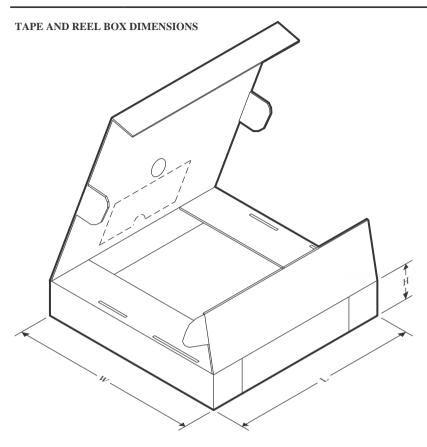


*All dimensions are nominal

| Device | | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|-------------|------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| CSD87312Q3E | VSON | DPA | 8 | 2500 | 330.0 | 12.4 | 3.6 | 3.6 | 1.2 | 8.0 | 12.0 | Q2 |

PACKAGE MATERIALS INFORMATION

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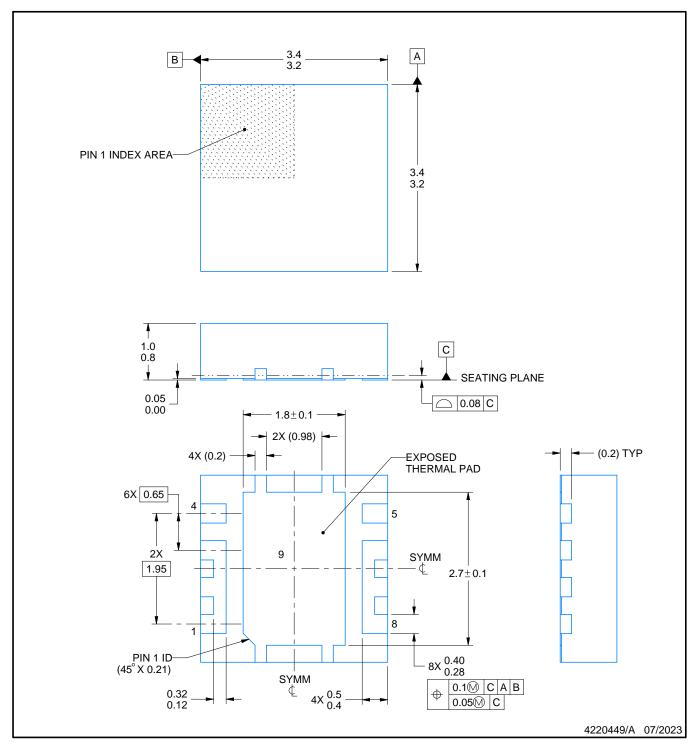


*All dimensions are nominal

| Device | Device Package Type | | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) | |
|-------------|---------------------|-----|------|------|-------------|------------|-------------|--|
| CSD87312Q3E | VSON | DPA | 8 | 2500 | 346.0 | 346.0 | 33.0 | |



PLASTIC SMALL OUTLINE - NO LEAD



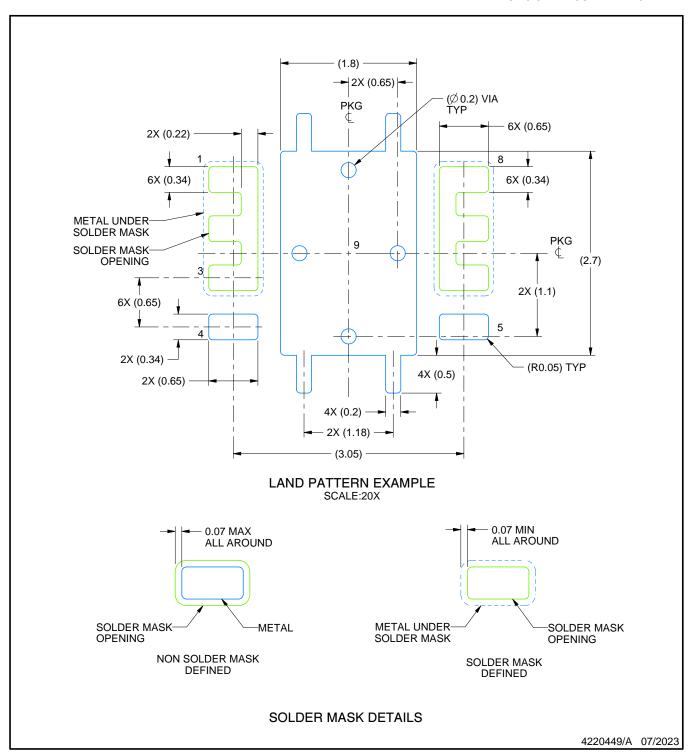
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC SMALL OUTLINE - NO LEAD

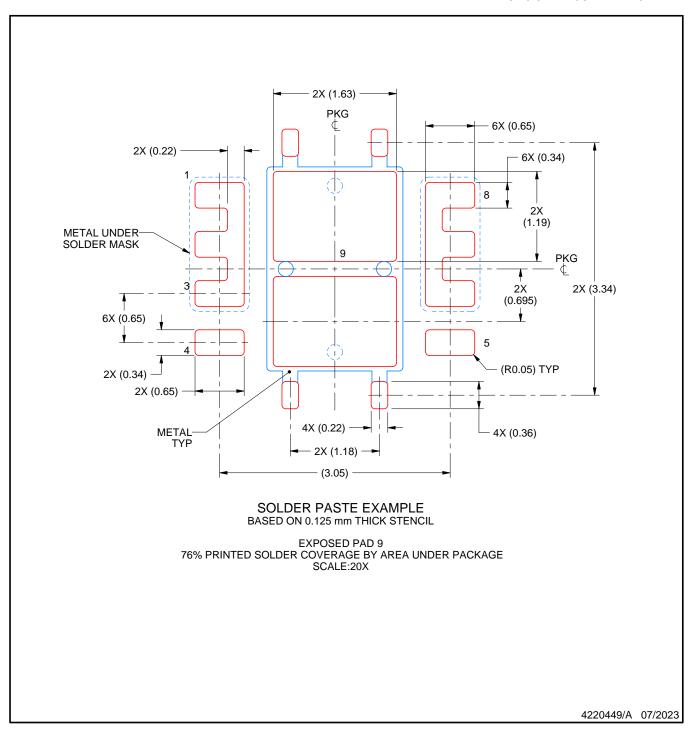


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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